

Exhibit I

IN THE CLAIMS:

Kindly amend the claims as follows.

11. (Twice Amended) A semiconductor device according to claim 13, wherein said transistor is a high voltage transistor[,] having a source diffusion layer within said source side offset diffusion layer region and a [said] drain diffusion layer [are high impurity concentration,] within said drain side offset diffusion layer region and said source side offset diffusion layer and said drain side offset diffusion layer [are lower in] have impurity concentrations lower than those of said source diffusion layer and said drain diffusion layer.

12. (Twice Amended) A semiconductor device according to claim 14, wherein said transistor is a high voltage transistor[,] having a source diffusion layer within said source side offset diffusion layer region and a [said] drain diffusion layer [are high impurity concentration,] within said drain side offset diffusion layer region and said source side offset diffusion layer and said drain side offset diffusion layer [are lower in] have impurity concentrations lower than those of said source diffusion layer and said drain diffusion layer.

13. (Amended) A semiconductor device comprising:

a source side offset diffusion layer region and a drain side offset diffusion layer region of a second conductivity type in a transistor formed, so as to be separated from each other, in a predetermined region in a region of a first conductivity type in a semiconductor substrate;

a gate insulator film [region] formed between said source side offset diffusion layer region and said drain side offset diffusion layer region;

a gate electrode formed on said gate insulator film [region]; and

a diffusion layer of the first conductivity type of which [the] an impurity concentration is higher than that of said region of the first conductivity type and which is formed so as to surround said source side offset diffusion layer region, said drain side offset diffusion layer region and said gate insulator film [region], wherein

both ends of said gate insulator film [region] in [the] a channel width direction [in the plan view,] form protruding portions that protrude at [the] borders of said source side offset diffusion layer region and of said drain side offset diffusion layer region in [the] a direction toward said diffusion layer of the first conductivity type so that said protruding

portions of said gate insulator film make direct contact with  
said gate electrode, and wherein

said diffusion layer of the first conductivity type is  
    formed so as not to be substantially present below said gate  
    insulator film [region] and is formed so as to be in contact with  
    said protruding portions.

14. (Amended) A semiconductor device comprising:

    a source side offset diffusion layer region and a drain side  
    offset diffusion layer region of a second conductivity type in a  
    transistor formed, so as to be separated from each other, in a  
    predetermined region in a region of a first conductivity type in  
    a semiconductor substrate;

    a gate insulator film [region] formed between said source  
    side offset diffusion layer region and said drain side offset  
    diffusion layer region;

    a gate electrode formed on said gate insulator film  
    [region]; and

    a diffusion layer of the first conductivity type of which  
    [the] an impurity concentration is higher than that of said  
    region of the first conductivity type and which is formed so as  
    to surround said source side offset diffusion layer region, said

drain side offset diffusion layer region and said gate insulator film [region], wherein

both ends of said gate insulator film [region,] in [the] a channel width direction [in the plan view,] form protruding portions that protrude at [the] borders of said source side offset diffusion layer region and of said drain side offset diffusion layer region in [the] a direction toward said diffusion layer of the first conductivity type so that said protruding portions of said gate insulator film make direct contact with said gate electrode, and wherein

said diffusion layer of the first conductivity type is formed so as to surround said protruding portions and so as to be separated from the protruding portions by a predetermined distance.